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# **Synchronous Mirror Delays**

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#### Introduction



- □ A synchronous mirror delay (SMD) is a type of clock generation circuit
- Unlike DLLs and PLLs an SMD is an open loop system
  - $\checkmark$  No clock jitter due to feedback and voltage oscillation
- □ SMDs have both analog and digital implementations
- □ An SMD is useful because it only requires two clock cycles to generate an internal clock synchronized to the external clock
  - ✓ Useful for application such as DRAM
  - ✓ Eliminates idle power consumption
  - ✓ Startup time is  $2 * T_{clk}$
- A major drawback of SMDs is that they must be designed for a specific buffer and propagation delay

# Digital Synchronous Mirror Delay



- The first type of implementation we will consider is the digital SMD (DSMD)
- □ The components of a DSMD are:
  - ✓ Input buffer
  - ✓ Delay monitor (DM)
  - ✓ Forward delay array (FDA)
  - ✓ Mirror control circuit (MCC)
  - ✓ Backward delay array (BDA)
  - ✓ Clock driver
- The circuit replicates the input clock by comparing the difference between the signal from the input buffer and the delay monitor



**DSMD** Block Diagram







#### DSMD Ideal Timing Diagram



 $tV = T_{clk} - (d_1 + d_2)$ 



**DSMD** Basic Circuit







### **DSMD** Calculations

Each delay element is a NAND gate and an inverter (an AND gate), the total array size can be determined by:

$$\checkmark T_{clk,max} = d_1 + d_2 + N * d_e$$

$$\checkmark N = \frac{T_{clk,max} - (d_1 + d_2)}{d_e}$$

□ The total delay from the input to the output is:

 $\sqrt{t_d} = d_1 + (d_1 + d_2) + \left[T_{clk} - (d_1 + d_2) + t_{Qe}\right] + \left[T_{clk} - (d_1 + d_2) + t_{Qe}\right] + d_2 = 2\left(T_{clk} + t_{Qe}\right)$ 

- The quantization error has a maximum value of one delay element (AND gate), this calculation ignores the delay from the NAND gate of the MCC.
- □ The clock period must be significantly larger than the delay monitor delay time (more specifically the width of the pulse must be larger than the delay time)

#### **DSMD** Calculations



- □ The delay element should be the minimum possible delay to minimize phase quantization error,  $t_{Oe}$
- □ The circuit on the next page has a  $d_e$  of 77 ps, the delay monitor  $(d_1 + d_2)$  is approximately 200 ps and it is designed for a minimum clock speed of 1 GHz ( $T_{clk,max} = 1$  ns) so N is 10.40 (11)
  - ✓ The circuit can actually operate at frequencies slightly lower than this as well due to the delay between the second and third delay elements
  - ✓ The output will begin to lead the input when it goes below the designed operating frequency
- □ For comparison a clock signal of 100 MHz would require N = 127.27 (128)!



## DSMD 800 MHz – 1.4 GHz Operating Range



### DSMD Simulation Results (800 MHz)





### DSMD Simulation Results (1 GHz)





#### DSMD Simulation Results (1.25 GHz)





#### DSMD Simulation Results (1.43 GHz)





# DSMD Advantages and Disadvantages



#### Advantages

- Easy to design/understand
- □ Fixed duty cycle
- Fast clock generation and short recovery time
- Power consumption only occurs during switching
- Works well for higher clock frequencies if delay element has a small delay

#### Disadvantages

- Array size is proportional to clock period
  - Lower clock speeds require a large array
  - Fine phase characteristics required for best accuracy
- Introduces a phase quantization error

# Analog Synchronous Mirror Delay



- We will now focus on an implementation of an analog SMD (ASMD)
- □ The components of an ASMD are:
  - ✓ Input buffer
  - ✓ Delay monitor (DM)
  - ✓ Clock divider
  - ✓ Charge pump and comparator
  - ✓ Clock driver
- □ The circuit replicates the input clock using charge pumps to oscillate the input voltage to the comparators
- □ The rising edge of the internal clock will not coincide with the external clock

#### ASMD Input Buffer and Timing Diagram





#### ASMD Charge Pump and Comparator











□ Using a 10 µA supply current and designing for a minimum clock frequency of 100 MHz

$$\checkmark C = \frac{I_{pump} * T_{clk}}{VDD} = 100 \, fF$$

During the period after the rising edge of the clock and before the signal has propagated through the DM (c = 1, d = 0)

$$\checkmark V_{left} = V_{ref}$$

□ After d goes high and before the falling edge of c (c = 1, d = 1) the capacitor charges at a rate of:

$$\frac{dV}{dV}$$
  $\frac{I}{dV}$   $\frac{1}{dV}$   $\frac{100 \, mV}{dV}$ 

 $\frac{dt}{dt} = \frac{1}{C} = \frac{1}{1 ns}$ 

□ When both control signals are low (c = 0, d = 0) the capacitor discharges at the same rate and measures the time it takes to cross  $V_{ref}$  and creates a pulse

## **ASMD** Operation



- □ It is clear from the schematic that when the charge pump causes the negative terminal of the comparator to drop below the reference voltage the output will go high
- ❑ A second circuit with the complemented signals connected to the control logic will cause a similar behavior 180° out of phase with the first signal.
- Using an OR gate we can replicate the input clock from these two signals.
- ❑ A major challenge with this architecture is matching the output duty cycle. If the pumping currents do not match exactly the duty cycle will change every clock period.

#### ASMD 100 MHz – 250 MHz Operating Range



Input Buffer and Clock Divider



**Charge Pumps** 

## ASMD Simulation Results (100 MHz)





### ASMD Simulation Results (160 MHz)





### ASMD Simulation Results (200 MHz)





#### ASMD Simulation Results (250 MHz)





## Improved ASMD Design



- Clearly this ASMD design is not practical nor useful
- □ There are four apparent problems with the ASMD shown
  - ✓ Duty cycle dependence on  $V_{ref}$
  - $\checkmark$  The up and down pumping mismatch
  - ✓ The circuit doesn't lock to the clock edge well
  - $\checkmark$  The timing mismatch from the control signals and their complements
- □ Replacing the positive comparator terminal  $V_{ref}$  connection with a second complemented pumping structure will cancel out the current mismatch for the comparator

$$\Delta t_{\text{dual}} = \frac{(\Delta \alpha + \Delta \beta) \cdot \{T_{\text{CLK}} - T_{\text{dm}}\}}{(\alpha + \beta + \Delta \alpha + \Delta \beta)}$$
$$\Delta t_{\text{single}} = \frac{(\beta + \Delta \beta - \alpha) \cdot \{T_{\text{CLK}} - T_{\text{dm}}\}}{(\beta + \Delta \beta)}$$





- Adding a transmission gate to the true control signals will improve the timing matching for the true and complemented signals
- □ The capacitance on the comparator inputs will also need to be increased slightly
- □ Layout size and power consumption increase, tradeoff for improved performance

## **Comparator Pump Timing Comparison**







# ASMD 100 MHz – 250 MHz Operating Range with Dual Pumping Scheme and TG Delay



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Charge Pumps

## ASMD Simulation Results (100 MHz)





### ASMD Simulation Results (160 MHz)





### ASMD Simulation Results (200 MHz)





40 ps jitter

### ASMD Simulation Results (250 MHz)





# Comparison of Single/Dual Pump ASMD



- □ The clock edge is now reliable (however the phase skew increases with frequency due to the internal delay of the comparator and pumping circuit)
- □ Jitter is greatly reduced
- Duty cycle mismatch is reduced
- Power consumption is increased
- □ Layout size is increased

# ASMD Advantages and Disadvantages



#### Advantages

- No delay array with a size dependency on clock period
- □ Fast clock generation and short recovery time
- □ Phase error is (ideally) zero
  - Due to the non-ideal nature of real circuits it is actually proportional to clock frequency
- Functions well at lower clock speeds

#### Disadvantages

- Requires a bias circuit
- Constantly consumes power (comparator and bias circuit)
- Duty cycle is modulated based on pump current and timing mismatches
- Some jitter is introduced due to timing mismatches

#### References



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- [2] Shim, D. et al, "An Analog Synchronous Mirror Delay for High-Speed DRAM Application," IEEE Journal of Solid-State Circuits, Vol. 34, pp. 484 – 493, Apr. 1999.
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- □ [4] Baker, R. Jacob, "CMOS Circuit Design, Layout and Simulation," 3<sup>rd</sup> edition, John Wiley & Sons, 2010.